

SANYO

No.2899

LA7321, 7321M

Monolithic Linear IC

**VHS VTR Playback Head Amp,
Recording Amp****Functions and Features**

(Functions) · 4-channel playback head amp

· 2-channel recording amp

· 13 head select switches (PB, REC)

· 1 recording amp gain select switch

· Envelope detector for special playback (for GT-4)

(Features) · Designed for 4 heads (for GT-4)

· On-chip head select switches, recording amp gain select switch, envelope detector for GT-4 making it possible to perform signal processing for the head section on a single chip.

· Load variations cause less recording current variations because of recording amp of constant-current type.

(Maximum recording current : 40mA_{pp})**Maximum Ratings at Ta = 25°C**

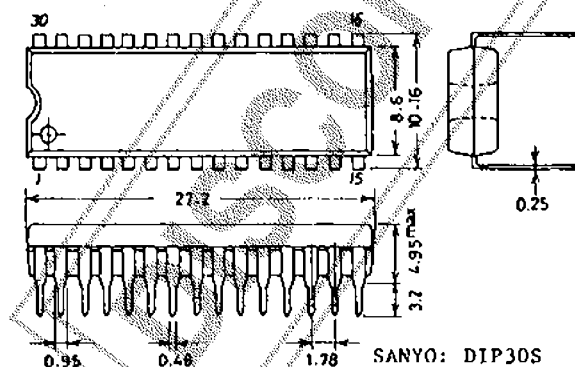
				unit
Maximum Supply Voltage	V _{CC} max	(PB)	7.0	V
		(REC)	14.0	V
Allowable Power Dissipation	P _d max	(65°C)	LA7321	920 mW
			LA7321M	850 mW
Operating Temperature	T _{opg}		-10 to +65	°C
Storage Temperature	T _{stg}		-40 to +125	°C

Operating Conditions at Ta = 25°C

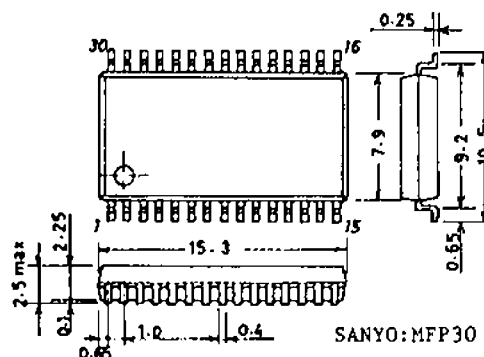
				unit
Supply Voltage	V _{CC}	(PB)	5.0	V
		(REC)	12.0	V
Operating Voltage Range	V _{CC} opg	(PB)	4.75 to 5.5	V
		(REC)	10 to 13	V

Case Outline 3061-D30S1C [LA7321]

(unit : mm)

**Case Outline 3073A-M301C [LA7321M]**

(unit : mm)



The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.

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N078TA, TS No.2899-1/9

Operating Characteristics at Ta = 25°C

Characteristic		Symbol	Test Conditions		SW				min	typ	max	unit
			Input	Output		1	2	3	4			
PB (Preamp Section)			T1		PB + 5V	SW 30	HA	EP /SP	Special MU			
Current Dissipation		I _{cep}			Pin 1 flow-in current	1	1	1	1	18	24	30 mA
Voltage Gain	CH1	VG (1)	T28	T7	Vi: 38mV _{pp} f: 1MHz	2	2	2	2	58.6	59.5	62.5 dB
	CH2	VG (2)	T27	T7		1	2	2	2			
	CH3	VG (3)	T23	T7		2	1	1	2			
	CH4	VG (4)	T21	T7		1	1	1	2			
Voltage Gain Difference 1		ΔVG (1)			VG (1) - VG (2)					-1.0	0	1.0 dB
Voltage Gain Difference 2		ΔVG (2)			VG (3) - VG (4)					-1.0	0	1.0 dB
Intermode Gain Difference		ΔVG SP-EP			VG (1) - VG (3)					-1.0	0	1.0 dB
Equivalent Input Noise Voltage	CH1	V _{NIN} (1)		T7	* $\frac{V_{out}}{VG(1),(2),(3),(4)}$ after 1.1MHz L.P.F.	2	2	2	2	1.1	1.5	μV _{rms}
	CH2	V _{NIN} (2)		T7		1	2	2	2			
	CH3	V _{NIN} (3)		T7		2	1	1	2			
	CH4	V _{NIN} (4)		T7		1	1	1	2			
Frequency Characteristic	CH1	ΔV _{fp} (1)	T28	T7	Vi: 38mV _{pp} f: 100kHz, 7MHz 7MHz 100kHz output ratio	2	2	2	2	-2.5	0	dB
	CH2	ΔV _{fp} (2)	T27	T7		1	2	2	2			
	CH3	ΔV _{fp} (3)	T23	T7		2	1	1	2			
	CH4	ΔV _{fp} (4)	T21	T7		1	1	1	2			
2nd Harmonic Distortion	CH1	V _{NIN} (1)	T28	T7	Vi: 38mV _{pp} f: 4MHz 8M component 4M component output ratio	2	2	2	2	-40	-35	dB
	CH2	V _{NIN} (2)	T27	T7		1	2	2	2			
	CH3	V _{NIN} (3)	T23	T7		2	1	1	2			
	CH4	V _{NIN} (4)	T21	T7		1	1	1	2			
Max. Output Level	CH1	V _{OM1} (1)	T28	T7	f: 1MHz Output level when 3rd distortion is -30dB.	2	2	2	2	0.8	1.0	V _{p-p}
	CH2	V _{OM2} (2)	T27	T7		1	2	2	2			
	CH3	V _{OM3} (3)	T23	T7		2	1	1	2			
	CH4	V _{OM4} (4)	T21	T7		1	1	1	2			

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Characteristic			Symbol		Test Conditions				SW				min	typ	max	unit
					Input	Output			1	2	3	4				
PB (Preamplifier Section)					T1		PB + 5V		SW 30	HA	EP /SP	Special MU				
Cross-talk 1 (SP)	CH1	V_{CR1} (1)	T27 T23 T21	T7	V_i : 38mVpp f: 4MHz V_{out}				2	2	2	1				
	CH2	V_{CR1} (2)	T28 T23 T21	T7	VG (1),(2) output ratio				1	2	2	1		-40	-35	dB
Cross-talk 2 (EP)	CH3	V_{CR2} (3)	T21 T28 T27	T7	V_i : 38mVpp f: 4MHz V_{out}				2	1	1	1				
	CH4	V_{CR2} (4)	T23 T28 T27	T7	VG (3),(4) output ratio				1	1	1	1		-40	-35	dB
Output DC Offset			ΔV_{ODC1}		Pin 7	CH1 - CH2			2→1	2		1				
			ΔV_{ODC2}		Pin 7	CH3 - CH4			2→1	1		1				
			ΔV_{ODC3}		Pin 7	CH1 - CH3			2	2→1		1				
			ΔV_{ODC4}		Pin 7	CH2 - CH4			1	2→1		1				
			ΔV_{ODC5}		Pin 7	CH1 - CH4			2→1	2→1		1				
			ΔV_{ODC6}		Pin 7	CH2 - CH3			1→2	2→1		1				
PB (Envelope Detector)					T1		PB + 5V									
Detection Pin DC Offset			$\Delta V_{b,s}$		T5 T6	T5(DC) - T6(DC)						1	-50	0	50	mV
Detection Characteristic 1 (SP)			V_{SDC}	T28	T5	After setting T7 output to f: 4MHz, V_i : 200mVpp, measure the difference between T5 output DC and T6 output DC at no input mode.			2	2		1	800	900	1000	mV
Detection Characteristic 2 (EP)			V_{SDC}	T23	T6	After setting T7 output to f: 4MHz, V_i : 200mVpp, measure the difference between T5 output DC and T6 output DC at no input mode.			2	1		1	800	900	1000	mV
Comparator Output Waveform 1			V_{SDC1}	T28	T9	V_i : 38mVpp f: 4MHz, T9 output DC			2	2		1	0	0.1	0.2	V
Comparator Output Waveform 2			V_{SDC2}	T23	T9	V_i : 38mVpp f: 4MHz, T9 output DC			2	1		1	3.8	4.0	4.2	V
REC					T14		REC + 12V									
Current Dissipation			I_{CCR}		T14	Pin 14 flow-in current						2	38	51	64	mA

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Characteristic		Symbol	Test Conditions		SW				min	typ	max	unit
			Input	Output		1	2	3				
REC			T14		REC+12V	SW 30	HA	EP /SP	Special MU			
Voltage Gain	EP C	VG(EC)	T10	T18	$V_i: 300\text{mVpp}$ $f: 1\text{MHz}$			1	2			
	EP Y	VG(EY)	T11	T18	$V_i: 300\text{mVpp}$ $f: 4\text{MHz}$			1	2			
	SP C	VG(SC)	T10	T16	$V_i: 300\text{mVpp}$ $f: 1\text{MHz}$			2	2	-8.0	-6.0	-4.0 dB
	SP Y	VG(SY)	T11	T16	$V_i: 300\text{mVpp}$ $f: 4\text{MHz}$			2	2			
Voltage Gain Difference 1		ΔV_G (EP)			$VG(EC) - VG(EY)$					-1.0	0	1.0 dB
Voltage Gain Difference 2		ΔV_G (SP)			$VG(SC) - VG(SY)$					-1.0	0	1.0 dB
Intermode Gain Difference		ΔV_G EP-SP			$VG(EC) - VG(SC)$					-1.0	0	1.0 dB
Frequency Characteristic	EP C	ΔV_{MR} (EC)	T10	T18	$V_i: 300\text{mVpp}$ $f: 1\text{MHz}, 7\text{MHz}$ 7M component			1	2			
	EP Y	ΔV_{MR} (EY)	T11	T18	1M component			1	2			
	SP C	ΔV_{MR} (SC)	T10	T16	output ratio			2	2	-2.0	-0.5	-1.0 dB
	SP Y	ΔV_{MR} (SY)	T11	T16				2	2			
2nd Harmonic Distortion	EP C	ΔV_{HDR} (EC)	T10	T18	$V_{out}: 30\text{mApp}$ (150mVpp)			1	2			
	EP Y	ΔV_{HDR} (EY)	T11	T18	$f: 4\text{MHz}$ 8M component			1	2			
	SP C	ΔV_{HDR} (SC)	T10	T16	4M component			2	2	-45	-40	dB
	SP Y	ΔV_{HDR} (SY)	T11	T16	output ratio			2	2			
Max. Output Level	EP C	V_{OMR} (EC)	T10	T18	$f: 4\text{MHz}$ Output level when 2nd harmonic distortion is -40dB.			1	2	30	40	mVpp
	EP Y	V_{OMR} (EY)	T11	T18				1	2			
	SP C	V_{OMR} (SC)	T10	T16				2	2			
	SP Y	V_{OMR} (SY)	T11	T16				2	2			
Muting Attenuation	EP C	V_{MR} (EC)	T10	T18	$V_i: 300\text{mVpp}$ $f: 1\text{M(C)}, 4\text{M(Y)}$ V_{out}			1	1			
	EP Y	V_{MR} (EY)	T11	T18	$VG(EC), (EY)$			1	1	-50	-45	dB
	SP C	V_{MR} (SC)	T10	T16	$(SC), (SY)$			2	1			
	SP Y	V_{MR} (SY)	T11	T16	output ratio			2	1			

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Characteristic			Symbol		Test Conditions		SW				min	typ	max	unit
							1	2	3	4				
REC			T14		REC +12V		SW 30	HA	EP /SP	Special MU				
Cross Modulation Relative Level	SP C	V_{CY} (EP)	T10 T11	T18	Input T10, $V_{out} = 40mV_{pp}, f = 629kHz$ Input T11, $V_{out} = 160mV_{pp}, f = 4MHz$ $4M \pm 629kHz$ 4MHz output ratio				1	2		45	-40	dB
	SP Y	V_{CY} (SP)	T10 T11	T16					2	2				
Switch Tr ON Resistance														
ON Resistance of SW Tr Turned ON at PB	SP	$R_{PON 30}$		T30	PB mode Difference between DC voltage at 1mA flow-in and DC voltage at 2mA flow-in $\times 1$							5	8	Ω
	EP	$R_{PON 19}$		T19										
ON Resistance of Mode Select SW Tr at PB	CH1	$R_{PON 28}$		T28	PB mode Difference between DC voltage at 1mA flow-in and DC voltage at 2mA flow-in $\times 1$				1	2		9	12	Ω
	CH2	$R_{PON 27}$		T27					1	2				
	CH3	$R_{PON 23}$		T23					2	2				
	CH4	$R_{PON 21}$		T21					2	2				
ON Resistance of SW Tr Turned ON at REC	SP	$R_{PON 30}$		T30	REC mode Difference between DC voltage at 1mA flow-in and DC voltage at 2mA flow-in				1			6	10	Ω
	EP	$R_{PON 19}$		T19					2					
Leak Current of Mode Select SW Tr at REC	SP	$I_L 30$		T30	REC mode Flow-in current when $\pm 5V$ is applied				2			-4	0	μA
	EP	$I_L 19$		T19					1					
ON Resistance of SW Tr Turned ON at REC	CH1	$R_{PON 28}$		T28	REC mode Difference between DC voltage at 1mA flow-in and DC voltage at 2mA flow-in $\times 1$							6	10	Ω
	CH2	$R_{PON 27}$		T27										
	CH3	$R_{PON 23}$		T23										
	CH4	$R_{PON 21}$		T21										
ON Resistance of Gain Select SW Tr at REC (SP)			R_{RSP}		T19 REC mode Difference between DC voltage at 1mA flow-in and DC voltage at 2mA flow-in $\times 1$				2			7	10	Ω

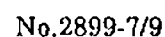
Note) $\times 1$ Let the ON resistance to be obtained be $x (\Omega)$,
 $2x (mV)$ at 2mA flow-in
 $1x (mV)$ at 1mA flow-in
Therefore, difference $2x - 1x = x$ is the ON resistance.

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Characteristic	Symbol	Test Conditions			SW				min	typ	max	unit
		Input	Output		1	2	3	4				
Control Pin Threshold Level at PB					SW 30	HA	EP /SP	Special MU				
SW 30 Threshold Level	SW 30 (1)	T28 T27	T2	CH1 → CH2 changeover voltage	※	2	2	2	2.5		5.0	V
	SW 30 (2)	T28 T27	T2	CH2 → CH1 changeover voltage					0		1.5	
HA Threshold Level	HA (1)	T28 T27	T3	CH1 → CH2 changeover voltage	2	※		1	2.5		5.0	V
	HA (2)	T28 T27	T3	CH1 → CH3 changeover voltage					0		1.5	
EP/SP Threshold Level	P _{MODE} (1)	T28	T4	T4 DC voltage when T7 output waveform disappears	2	2	※	2	2.5		5.0	V
	P _{MODE} (2)	T28	T4	T4 DC voltage when T7 output waveform appears					0		1.5	
Special PB "II" Threshold Level	Special (1)	T28 T27	T13	T13 DC voltage when T7 output waveform appears	2	2	1	※	3.0		5.0	V
	Special (2)	T28 T27	T13	T13 DC voltage when T7 output waveform disappears					0		1.5	
Control Pin Threshold Level at REC												
EP/SP Threshold Level	P _{MODE} (1)	T10	T4	T4 DC voltage when output changes from T16 to T18			※	2	2.5		5.0	V
	P _{MODE} (2)	T10	T4	T4 DC voltage when output changes from T18 to T16					0		1.5	
Threshold Level at REC MUTE	MUTE (1)	T10	T13	T13 DC voltage when T18 output waveform disappears			1	※	3.0		5.0	V
	MUTE (2)	T10	T13	T13 DC voltage when T18 output waveform appears					0		1.5	

LA7321,7321M Block Diagram



LA7321,7321M

LA7321,7321M Pin Description

Pin No.	Function	Standard DC Voltage	Input/Output Configuration	Remarks
1	PB + 5V			24mA typ.
2	SW30 control pin			L : 0 to 1.5V H : 2.5 to 5.0V
3	H · A control pin			L : 0 to 1.5V H : 2.5 to 5.0V
4	control pin			L : 0 to 1.5V H : 2.5 to 5.0V
5 · 6	Envelope detection pin	2.4 (V)		
7	Preamp output	2.3 (V)		· Connect R = 2kΩ externally when the output line is routed around.
8	GND			
9	(PB) Comparator output (REC) SW pin for gain change			※ SW Tr ON resistance 7 to 10Ω ※ For gain change, refer to pin 12.
10 · 11	REC amp input chroma. Y	6.7 (V)		Rin = 10kΩ
12	REC Y/CMIX amp feedback pin	5.9 (V)		※ The gain depends on R1. R1 : 180 = 10.5dB ※ R2 can be used to change the gain. R2 : 500 = +2.0 : 200 = +3.7dB (R : 1.2kΩ)

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Pin No.	Function	Standard DC Voltage	Input/Output Configuration	Remarks
13	(PB) Special PB control pin (REC) REC MUTE control pin			L : 0 to 1.5V II : 3.0 to 5.0V
14	REC +12V			
15 16 17 18	REC Amp output Amp feedback pin	5.9 (V)		· Maximum REC current 40mApp
19 30	PB ON SW Tr REC mode select SW Tr			On resistance 6 to 10Ω
20 24 26 29	Preamplifier bypass capacitor pin	1.9 (V)		· The gain depends on R1. R1 : 0 = 0dB : 820 = -3dB : 1.2k = -4dB
21 23 27 28	Preamplifier input	0.7 (V)		· Rin ≅ 400Ω · Cin ≅ 40 to 50p
22	REC circuit check pin			ON resistance 6 to 10Ω
25	Pre GND			